UNISONIC TECHNOLOGIES CO., LTD

UT6898 Power MOSFET

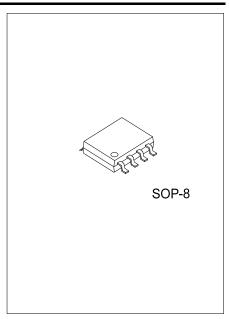
N-CHANNEL ENHANCEMENT

■ DESCRIPTION

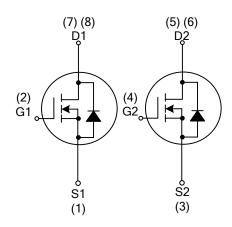
The **UT6898** uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

- * $R_{DS(ON)}$ <18 m Ω @ V_{GS} =4.5V, I_D =9.4A
- * $R_{DS(ON)}$ <14 m Ω @ V_{GS} =2.5V, I_D =8.3A
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified



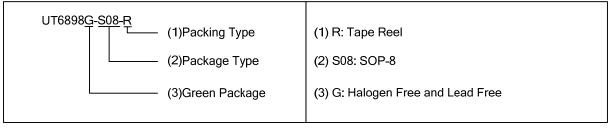
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment							Dealing	
		1	2	3	4	5	6	7	8	Packing
UT6898G-S08-R	SOP-8	S	G	S	G	D	D	D	D	Tape Reel

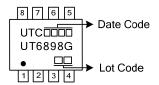
Note: Pin Assignment: G: Gate D: Drain S: Source



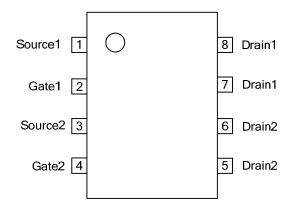
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UT6898

■ MARKING



■ PIN CONFIGURATION



UT6898

■ **SOLUTE MAXIMUM RATINGS** (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current	I _D	9.4	Α
Pulsed Drain Current	I _{DM}	38	Α
Maximum Power Dissipation	P_{D}	2	W
Junction Temperature	TJ	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to-Case	θ_{JC}		40		°C/W

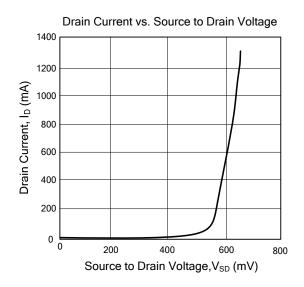
■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT					
OFF CHARACTERISTICS											
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_{D} =250 μ A	20			V					
Drain-Source Leakage Current	I_{DSS}	V _{GS} =0V, V _{DS} =16V			1	μΑ					
Gate-Source Leakage Current	I_{GSS}	V_{GS} =±12V, V_{DS} =0V,			±100	nA					
ON CHARACTERISTICS (Note 1)											
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.5	1	1.5	V					
On State Drain Current	$I_{D(ON)}$	V_{GS} =4.5 V, V_{DS} =5V,	19			Α					
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =4.5V, I _D =9.4A		10	14	m0					
		V _{GS} =2.5V, I _D =8.3A		13	18	mΩ					
DYNAMIC CHARACTERISTICS											
Input Capacitance	C _{ISS}			1821		pF					
Output Capacitance	Coss	V_{GS} =0V, V_{DS} =10V, f=1MHz		440		pF					
Reverse Transfer Capacitance	C_{RSS}			208		pF					
SWITCHING PARAMETERS (Note 1)											
Turn-ON Delay Time	$t_{D(ON)}$			10	20	ns					
Turn-ON Rise Time	t_R	V_{GS} =4.5 V , V_{DS} =10 V , I_{D} =1 A		15	27	ns					
Turn-OFF Delay Time	t _{D(OFF)}	R_{GEN} =6 Ω		34	55	ns					
Turn-OFF Fall-Time	t_{F}			16	29	ns					
Total Gate Charge	\mathbf{Q}_{G}	\ -4.5\(\)\ -4.0\(\)		16	23	nC					
Gate Source Charge	Q_{GS}	V _{GS} =4.5V, V _{DS} =10V,		3		nC					
Gate Drain Charge	Q_GD	ID-9.4A		4		nC					
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS											
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} =0V, I _S =1.3A (Note 1)			1.3	V					
Maximum Continuous Drain-Source Diode Forward Current	Is			0.7	1.2	Α					

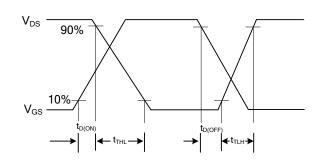
Notes: 1. Pulse Test: Pulse Width < 300ms, Duty Cycle < 2.0%

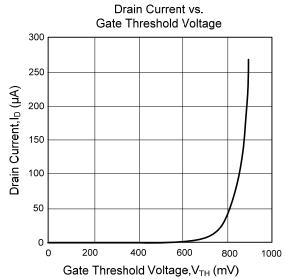
2. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied

■ TYPICAL CHARACTERISTICS

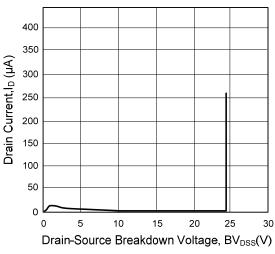


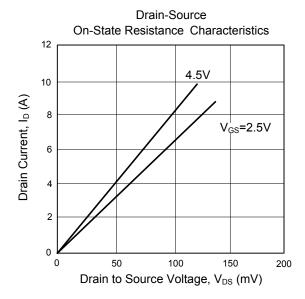
Switching Time Waveforms





Drain Current vs.
Drain-Source Breakdown Voltage





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